Effect of strong localization of doped holes in angle-resolved photoemission spectra of La$_{1-x}$Sr$_x$FeO$_3$


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We have performed an angle-resolved photoemission spectroscopy study of La$_{0.8}$Sr$_{0.2}$FeO$_3$ using in situ prepared thin films and determined its band structure. The experimental band dispersions could be well explained by an empirical band structure assuming the G-type antiferromagnetic state. However, the Fe 3d bands were found to be shifted downward relative to the Fermi level ($E_F$) by $\sim 1$ eV compared with the calculation and to form a (pseudo)gap of $\sim 1$ eV at $E_F$. We attribute this observation to a strong localization effect of doped holes due to polaron formation.

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Metal-insulator (MI) transitions in strongly-correlated electron systems have been generally understood in terms of band-width control and filling control. However, the actual situation is more complicated because of the effect of disorder, electron-phonon interaction, charge and orbital ordering, etc. Electron-phonon interaction causes a polaronic effect on charge carriers and increases their effective masses. In some filling-controlled systems, carriers doped into the Mott insulator remain localized as self-trapped small polarons and the system remains insulating. The problem of how an MI transition occurs when strong electron-phonon interaction is present remains highly controversial. A striking example is a hole-doped Mott insulator (charge-transfer-type insulator) La$_{1-x}$Sr$_x$FeO$_3$ (LSFO), where the insulating phase is unusually wide in the phase diagram ($0 < x < 0.5$ at room temperature and $0 < x < 0.7$ at low temperatures). In a previous photoemission study, the gap at the Fermi level ($E_F$) was seen for all compositions in the range $0 \leq x \leq 0.67$, consistent with the wide insulating region.

The effect of electron-phonon interaction is clearly reflected on the spectral function, and recent photoemission results have been discussed in this context for high-$T_c$ superconductors, Mn oxides, VO$_2$, and Fe$_3$O$_4$. Angle-resolved photoemission spectroscopy (ARPES) is a particularly powerful technique by which one can directly study the band structure of a material. However, there have been few studies on transition metal oxides (TMOs) with the cubic perovskite structures like LSFO because many of them do not have a cleavage plane. Recently, the band structure of the three-dimensional perovskite La$_{1-x}$Sr$_x$MnO$_3$ has been studied by ARPES using well-defined surfaces of in situ prepared epitaxial thin films, demonstrating that such an approach on TMO films is one of the best methods for such a purpose. In this paper, we report on in-situ ARPES results of single-crystal LSFO ($x = 0.4$) thin films grown on SrTiO$_3$ (001) substrates. We observed several dispersive bands which can be assigned to the Fe 3d $e_g$, $t_{2g}$ and O 2p bands. The experimental band structure was interpreted based on an empirical tight-binding band structure assuming the G-type antiferromagnetic (AF) state. In spite of the overall agreement between experiment and theory, fundamental discrepancies were found for the overall shift of the Fe 3d bands away from $E_F$ and the suppression of spectral weight around $E_F$. We shall discuss these discrepancies in terms of strong polaronic effect.

Experiment was carried out using a photoemission spectroscopy (PES) system combined with a laser molecular beam epitaxy (MBE) chamber at beamline BL-1C of the Photon Factory, KEK. The LSFO ($x = 0.4$) thin films were grown epitaxially on Nb-doped SrTiO$_3$ substrates by the pulsed laser deposition method. Details are described in Ref. 5. The lattice constants were determined to be $a = b = 3.905$ Å and $c = 3.883$ Å. In this paper, $k_{\parallel}$ denotes the in-plane electron momentum, and $k_z$ the out-of-plane one, expressed in units of $\pi/a$ or $\pi/c$. By low energy electron diffraction, sharp 11 spots were observed with no sign of surface reconstruction. ARPES measurements were performed under ultrahigh vacuum of $\sim 10^{-10}$ Torr at 150 K, below the Néel temperature ($T_N = 320$ K) of LSFO with $x = 0.4$, using a Scienta SES-100 electron energy analyzer. The total energy resolution was set to about 150 meV. The $E_F$ position was determined by measuring gold spectra.

Figure 1 shows ARPES spectra of an LSFO ($x = 0.4$) thin film taken with a photon energy of 74 eV. The inset shows a trace in k-space for $h\nu = 74$ eV with changing polar emission angle $\theta$. Here, we have assumed the work function of the sample $\phi = 4.5$ eV, and the inner potential $V_0 = 10.5$ eV so that the periodicity of the band dispersion is correctly given in normal emission (not shown).
FIG. 1: ARPES spectra of an LSFO ($x = 0.4$) thin film taken at $h\nu = 74$ eV. Polar angle ($\theta$) referenced to the surface normal is indicated. The inset shows the trace in $k$-space.

The shoulder structure at $\sim -1.3$ eV shows a significant dispersion, and is assigned to the Fe 3$d$ majority-spin $e_g$ bands. The peak structure at $\sim -2.4$ eV shows a weaker dispersion, and is assigned to the Fe 3$d$ $t_{2g}$ majority-spin bands. The structures at $-(4 - 7)$ eV show strong angular dependence and are assigned to O 2$p$ bands. The $e_g$ bands do not cross $E_F$, consistent with the insulating behavior and the persistence of the gap observed in the angle-integrated PES (AIPES) spectra [8].

The band dispersions are more clearly seen in the grayscale plot in the left panel of Fig. 2(a). Here, the second derivatives of the energy distribution curves (EDCs) are plotted on the gray scale with dark parts corresponding to energy bands. The same plot for $h\nu = 88$ eV [corresponding to the upper trace in Fig. 2(c)] is shown in the left panel of Fig. 2(b). In Fig. 2(c), hole pockets obtained by the tight-binding calculation (described below) are also shown. The trace for 74 eV crosses the calculated hole pocket at $k_{\parallel} \sim 1.5\pi/a$, while that for 88 eV does not in the same $k_{\parallel}$ region. Figure 3 shows enlarged grayscale plots near $E_F$ in $E$-$k$ space. Panel (a) is a direct intensity plot of the EDCs in Fig. 1. Angle-independent part has been subtracted as a background. Second derivatives of the EDCs are produced in panel (b) and those of momentum distribution curves (MDCs) in panel (c). In all the plots, the band has a minimum at $k_{\parallel} \sim 2.0\pi/a$, and disperses upward toward both sides and disappears at $k_{\parallel} \sim 1.5\pi/a$ and $k_{\parallel} \sim 2.5\pi/a$, not at $E_F$ but $\sim 1$ eV below it.

In order to interpret the experimental band dispersions more quantitatively, we performed a tight-binding band-structure calculation with empirical parameters, following the scheme in Refs. [13, 14, 15]. We performed the calculation, however, assuming the G-type AF state cor-

FIG. 2: Comparison of the ARPES spectra of LSFO taken at 74 eV (a) and 88 eV (b) with tight-binding calculation. The left panels show the experimental band structure deduced from the second derivatives of the EDCs (dark parts correspond to energy bands) and the right panels show the result of tight-binding calculation, taking into account the finite photoelectron mean-free path. The traces in $k$-space and calculated hole pockets are shown in (c).

FIG. 3: Enlarged plot of ARPES spectra near $E_F$ in $E$-$k$ space. Panel (a): Intensity plot of the EDCs. Angle-independent part has been subtracted as a background. (b): Second derivatives of the EDCs. (c): Second derivatives of the MDCs. (d): Result of tight-binding calculation. White dotted curves are the guide to the eye.
responding to the magnetic ordering in LSFO. Here, the
effect of G-type antiferromagnetism was taken into
account phenomenologically by imposing an energy difference \( \Delta E \) between the spin-up and spin-down Fe sites.
Parameters to be fitted were therefore \( \Delta E \), the en-
ergy difference between the Fe 3d level and the O 2p
level, \( \epsilon_p - \epsilon_d \), and a Slater-Koster parameter, \((pd\sigma)\) [10]. For the other Slater-Koster parameters, we as-
sumed \((pd\sigma)/(p\sigma\sigma) = -2.2 \) [17,18], and \((p\sigma\sigma) \) and \((p\sigma\pi) \) were taken to be 0.60 eV and -0.15 eV, respectively [10]. 
\((pd\sigma) \) is expected in the range of \(- (1.4 - 1.9) \) eV from a
configuration-interaction (CI) cluster-model calculation
\[\text{Ref.}\] [3,10]. Crystal-field splitting \( 10D_q \) of 0.41 eV was taken
from Ref. [3]. It should be noted that \( \epsilon_p - \epsilon_d \), \((pd\sigma) \) and
\( \Delta E \) primarily determine the Fe 3d – O 2p band positions,
their dispersions, and the optical band gap, respectively,
and therefore can be rather uniquely determined.

The best fit to the observed band dispersions of LSFO
and the optical gap 2.1 eV of LaFeO\(_3\) (LFO) [21] as shown in
the right panels of Fig. 2 (a) and (b) has been ob-
tained for reasonable parameter values \( \epsilon_p - \epsilon_d = 0 \) eV,
\((pd\sigma) = -1.5 \) eV, and \( \Delta E = 5.3 \) eV. For these plots, we have considered the effect of \( k_z \) broadening \( \langle \Delta k_f \rangle \)
caused by a finite escape depth \( \lambda \) of photoelectrons [21]
\[\lambda_k \sim 1/\lambda \sim 0.2 \text{ Å}^{-1} \] is approximately 10 \% of the
Brillouin zone \( (2\pi/c) \). The dispersions of the \( e_g \) bands
were thus successfully reproduced. The weak dispersions
of the \( t_{2g} \) bands and the width of the O 2p bands were also
well reproduced by these parameters. According to the
band-structure calculation, spectral weight should be cut
off above the calculated \( E_F \), which is determined by the
band filling for \( x = 0.4 \), while in experiment it gradually
decreases from the calculated \( E_F \) toward the experimen-
tal \( E_F \). This discrepancy inevitably arises from the fact
that this material is insulating up to 70 \% hole doping
while the rigid-band model based on the present band
structure gives the metallic state.

Figure 3 (a) shows the density of states (DOS) of the
G-type AF state calculated using the same parameter
set. The partial DOS’s for the majority-spin Fe \( e_g \),
the majority-spin \( t_{2g} \), the minority-spin \( e_g \), and the minority-
spin \( t_{2g} \) orbitals are shown in the lower panels. A large
band gap opens between the occupied majority-spin \( e_g \)
bands and the unoccupied minority-spin \( t_{2g} \) bands for the
present \( \Delta E \) value. These characteristic features were al-
ready reported by the previous Hartree-Fock calculation
[22] and the local spin-density-approximation calculation
[23]. In Figs. 2 and 4 \( E_F \) for \( x = 0.4 \) has been determined
from the filling of electrons when holes are doped into the
AF insulator. In Figs. 3 (b) and (c) the calculated results
are compared with the combined AIPES and O 1s x-ray
absorption (XAS) spectra of LFO and LSFO \( (x = 0.4) \),
respectively [3]. For LFO, the three main structures of
the valence band, \( A \), \( B \), and \( C \) are successfully repro-
duced by the calculation, while the satellite structure
in the valence-band photoemission spectrum could not
be reproduced. The crystal-field splitting into D and E
above \( E_F \) is also well reproduced. For LFO, although the
calculated band gap has been adjusted to the experi-
tmental value, the peak positions of structures A and E
are still shifted away from \( E_F \) in the experiment compared
to the calculation [as denoted by broken lines in Fig. 4
(b)]. As for \( x = 0.4 \) [Fig. 3 (c)], structure \( A \) is shifted away
from \( E_F \) compared to the calculation even more.

Generally speaking, doped holes may be localized due
to disorder or through coupling to lattice distortion.
The latter effect, namely, polaronic effect was recently ob-
served in the photoemission spectra of a number of TMOs
[2,4,13,14]. Note that for \( x = 0.4 \) a hole-induced peak
F appears within the band gap of LFO and accomodates
doped holes. These observations cannot be explained by
the rigid-band model in which \( E_F \) has been shifted ac-
cording to the band filling. The breakdown of the rigid-
band model means that doped holes do not enter the top
of the \( e_g \) majority-spin band but enter localized states
split off from the top of the \( e_g \) band, causing the insulat-
ning behavior of this material.

Finally, we further discuss the discrepancy between
the band-structure calculation and the experimental re-
sults near \( E_F \) and the origin of the insulating behavior
of LSFO. Figure 5 schematically shows the calculated
and experimental band structure and DOS of LSFO. Our
tight-binding calculation is similar to local-density ap-
proximation (LDA) \( +U \) in the sense that the effect of
electron-electron interaction and hence the value of the
band gap is adjusted via \( \Delta E \) in the tight-binding cal-
culation and via \( U \) in the LDA \( +U \) calculation. Bro-
ned lines indicate the tight-binding or LDA \( +U \) band
structure, where the value of the band gap of the par-
ent insulator has been adjusted to \( \sim 2 \) eV in order to
reproduce the optical gap [20]. When holes are doped
into this system, \( E_F \) moves downward and crosses the
\( e_g \) band, making the system metallic if the rigid-band
model can be applied. However, from the comparison
of calculation and experiment in Figs. 2 and 4 the \( e_g \) struc-
tures are shifted away from \( E_F \), and hole-induced states
appear above \( E_F \). The existence of these hole-induced
states means that the rigid-band model is no more valid,
and doped holes enter split-off localized states formed by
hole doping. There is also a spectral line-shape broadening compared to the band-structure calculation. Such a modification of the structures and line-shape broadening have been attributed to a polaronic effect recently observed in a number of TMOs [2, 3, 4]. For example, in the case of Ca$_{2-x}$Na$_x$CuO$_2$Cl$_2$, the spectral weight of quasiparticle peak $Z$ becomes extremely small due to a strong coupling to phonons [2]. In the case of VO$_2$ [5] and Fe$_3$O$_4$ [6], spectral changes with temperature were interpreted by considering strong coupling of electrons to phonons. In the case of LSFO, we consider that electron-phonon coupling is very strong for the $e_g$ orbitals compared to the $t_{2g}$ orbitals, the effect can be dramatic as observed in LSFO, where doped holes have $e_g$ character. Moreover, according to the temperature-dependent PES and XAS studies, short-range (local) charge order may exist in the wide composition range [24]. The polaronic effect probably enhances the tendency toward local charge ordering and explains the unusually wide insulating phase in LSFO.

In summary, we have performed an in-situ ARPES study on single-crystal LSFO ($x = 0.4$) thin films and determined its band structure. The observed dispersive bands were assigned to Fe $3d_{xy, yz}$, $t_{2g}$ and O $2p$ bands. The experimental band dispersions were interpreted using a tight-binding band-structure calculation by assuming the G-type antiferromagnetic state. From the discrepancy near $E_F$ between experiment and theory in spite of the overall agreement, the insulating behavior of this material is proposed to be caused by the localization of hole-induced states due to polaronic effect and/or short-range charge order.

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FIG. 5: Schematic picture of polaronic effects and hole-induced states in LSFO. (a) Band dispersions, (b) DOS.


The effect of $k_z$ broadening is given by the following Lorentzian function, $L(k_z) = 1/\{(k_z - k_{z0})^2 + (1/2\lambda)^2\}$, where $\lambda$ denotes an escape depth of photoelectrons. Here we used the value $\lambda = 5$ Å.